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(54) Title: ENABLING SCANNING ELECTRON MICROSCOPE IMAGING WHILE PREVENTING SAMPLE DAMAGE ON SENSITIVE LAYERS USED IN SEMICONDUCTOR MANUFACTURING PROCESSES

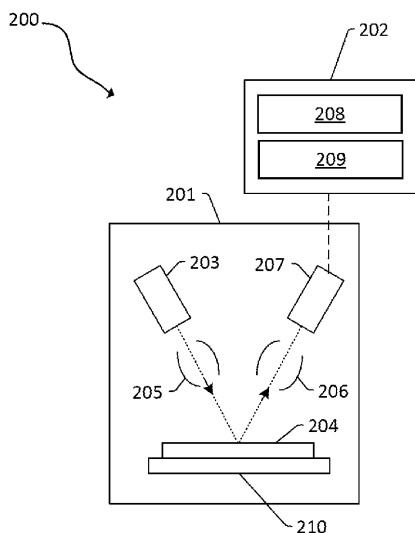


FIG. 7

(57) Abstract: During electron beam imaging of a semiconductor wafer, the electron beam is adjusted to a first electron dose/nm²/time value below a damage threshold for an image frame grab of a site on the semiconductor wafer. Then the electron beam is adjusted to a second electron dose/nm²/time value different from the first electron dose/nm²/time value for a second image frame grab of the site. The second electron dose/nm²/time value can be above the damage threshold.

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